

forming, on an underlying wiring, a barrier metal film of a metal whose conductivity will not be lost when the metal is oxidized;

forming a seed layer in contact with the barrier metal film; and

forming a conductive film as an upper-layer wiring, such that conductive film is in contact with the seed layer.

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cont.

22. (Amended) The method of Claim 21, wherein the metal whose conductivity will not be lost when the metal is oxidized is Ru, Ir or an alloy containing Ru or Ir.

B2 24. (Amended) The method of Claim 21, wherein the seed layer is composed of copper or a copper alloy.

B3 32. (Amended) The method of Claim 21 further comprising the step of, after forming the conductive film, forming the upper-layer wiring by etching the conductive film using a mask pattern covering a wiring forming region.

Please add the following new claims 33-38

-- 33. (New) The method of Claim 21, wherein the barrier metal film includes a conductive metal oxide.

B4 34. (New) The method of Claim 21, wherein in the step of forming the conductive film, the barrier metal film is oxidized to form a metal oxide film

35. (New) A method for fabricating a semiconductor device comprising the steps of :

forming, on an underlying wiring, a barrier metal film composed of a conductive metal oxide;

forming a seed layer in contact with the barrier metal film, and

forming a conductive film as an upper-layer wiring, such that the conductive film is in contact with the seed layer,

wherein the seed layer is composed of the same metal as the conductive film.

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cont. 36. (New) The method of Claim 35, wherein the conductive metal oxide is RuO₂, IrO₂ or an alloy oxide containing Ru or Ir.

37. (New) The method of Claim 35, wherein the seed layer is composed of copper or a copper alloy.

38. (New) The method of Claim 35 further comprising the step of, after forming the conductive film, forming the upper-layer wiring by etching the conductive film using a mask pattern covering a wiring forming region. --

REMARKS

The Examiner's Office Action dated October 4, 2002 has been received and its contents carefully noted. The Applicants respectfully submit that this response is timely filed and fully response to the Office Action. By the above amendments, claims 21, 22, 24 and 32 have been amended, new claims 33-38 have been added, and claims 23 and 25-31 have been canceled. Consequently, claims 21, 22, 24, 32-38 are currently pending.

With regard to the Examiner's rejections of:

Claims 21, 22 and 24-26, under 35 U.S.C. 102(a/e), as being anticipated by the teachings of Soininen et al.(Pub. Appl. '293), and